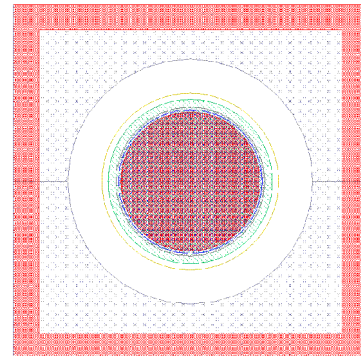


## 2KG026075YQ SWITCHING DIODE CHIPS

### DESCRIPTION

- 2KG026075YQ is a high speed switching diode chip fabricated in planar technology.
- This chip can be encapsulated as 1N4148 switching diode.
- When the chip is selected glass package, the chip thickness is 100 $\mu$ m, and the top electrodes material is Ag bump, the back-side electrodes material is Ag.
- Chip size: 0.26 X 0.26 (mm)<sup>2</sup>.

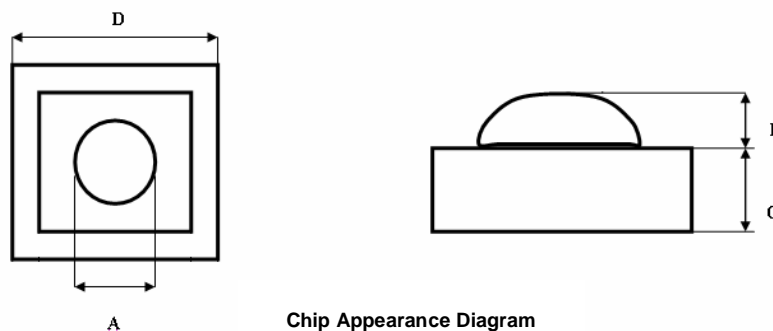


2KG026XXX CHIP TOPOGRAPHY

### 2KG026075YQ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C)

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =10mA.	--	--	1.0	V
		I <sub>F</sub> =100mA.	0.62	0.9	1.2	V
Reverse Voltage	V <sub>BR</sub>	I <sub>B</sub> =100 $\mu$ A.	100	120	--	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =20V.	--	--	25	nA
		V <sub>R</sub> =75V.	--	--	5	$\mu$ A
Diode Capacitance	C <sub>d</sub>	f=1MHz; V <sub>R</sub> =0.	--	1.9	4	pF
Reverse Recovery Time	t <sub>rr</sub>	When switched from I <sub>F</sub> =10mA to V <sub>R</sub> =6V; R <sub>L</sub> =100 $\Omega$ ; measured at I <sub>R</sub> =1mA.	--	--	4	ns

### 2KG026075YQ APPEARANCE (Top side material is Ag ball)



Chip Appearance Diagram

Parameter	Symbol	Min.	Type	Max.	Unit
Chip Size	D	220	--	240	$\mu$ m
Chip Thickness	C	85	--	120	$\mu$ m
Bump Diameter	A	135	--	160	$\mu$ m
Bump Height	B	20	--	40	$\mu$ m
Scribe Line Width	/	--	40	--	$\mu$ m